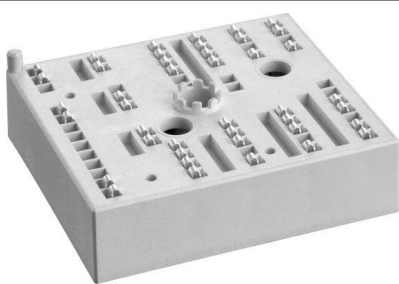


SKiiP 28ANB16V2



MiniSKiiP® 2

3-phase bridge rectifier +
brake chopper

SKiiP 28ANB16V2

Features

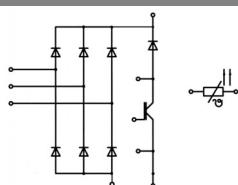
- Fast Trench IGBTs
- Robust and soft freewheeling diodes in CAL technology
- Highly reliable spring contacts for electrical connections
- UL recognised file no. E63532

Typical Applications

- Input bridge for Inverter up to 39 kVA

Remarks

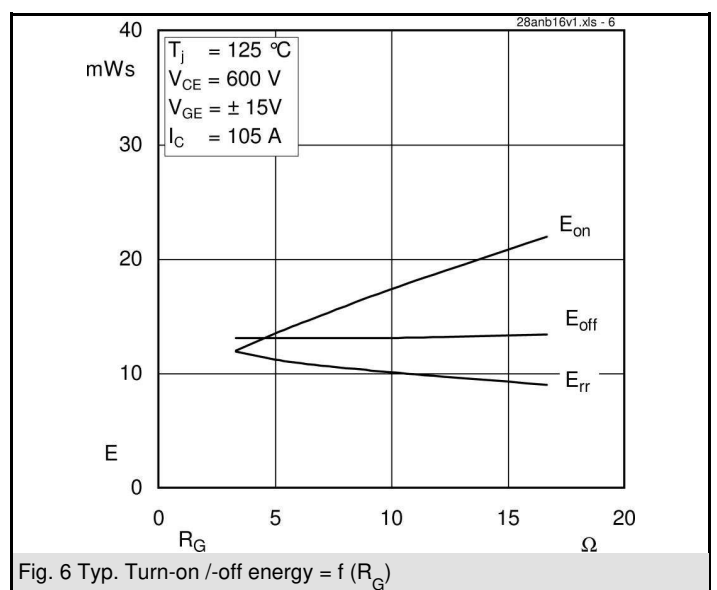
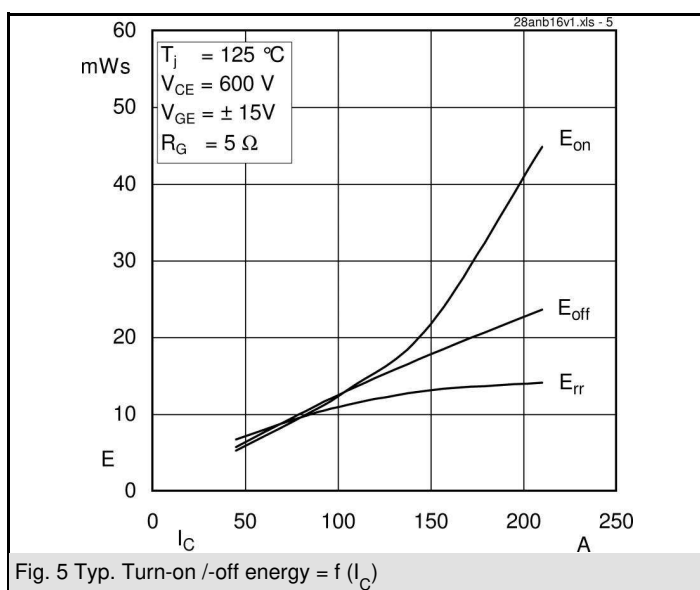
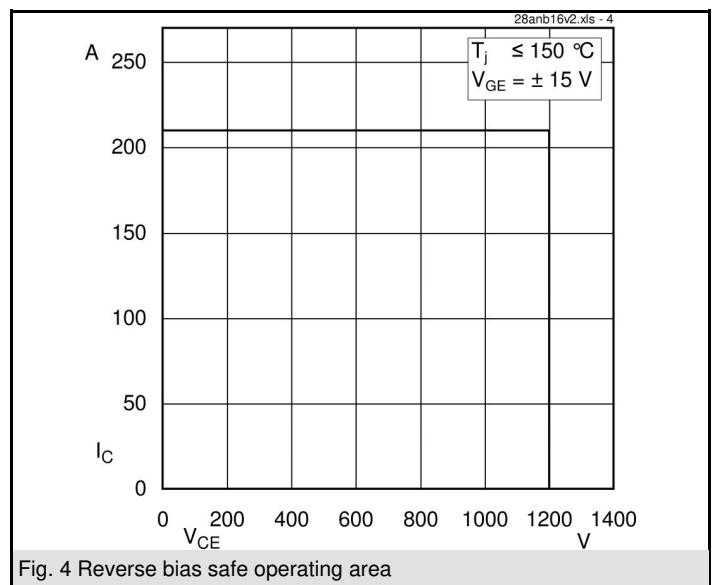
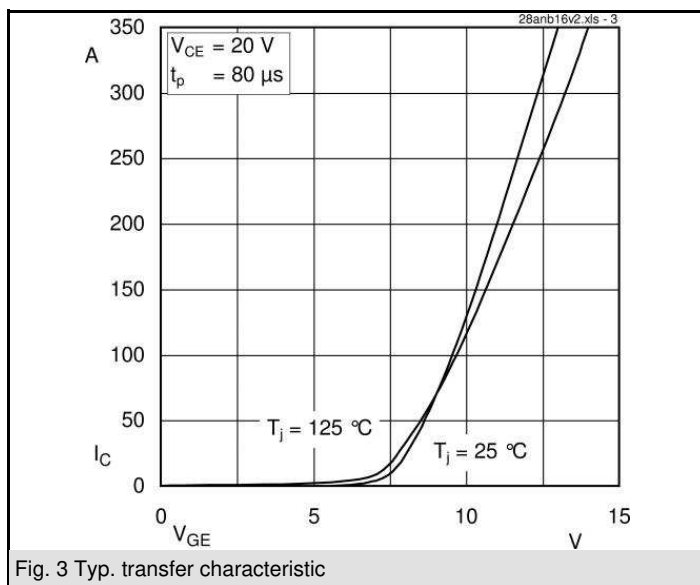
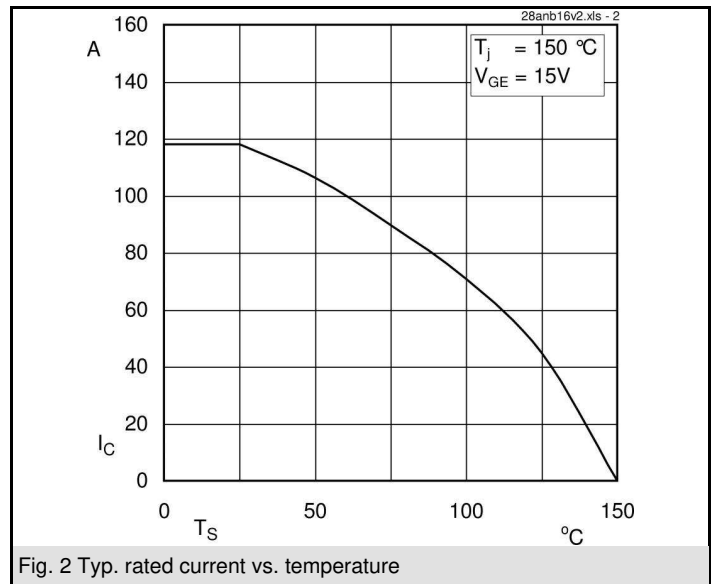
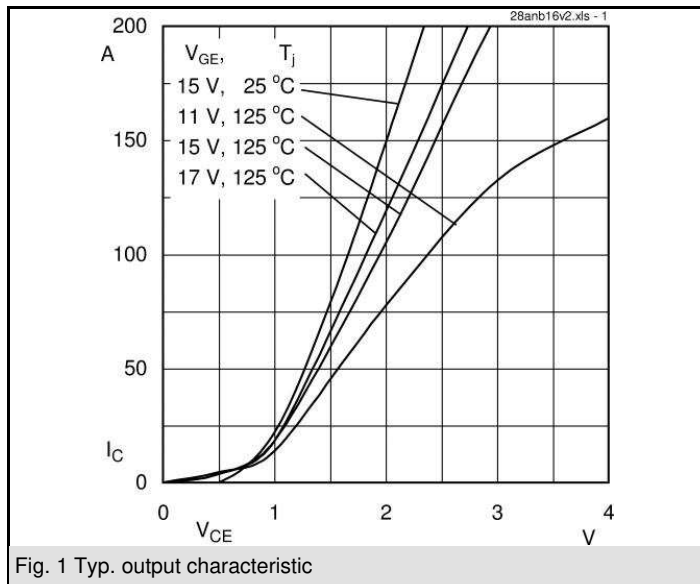
- V_{CEsat} , V_F = chip level value

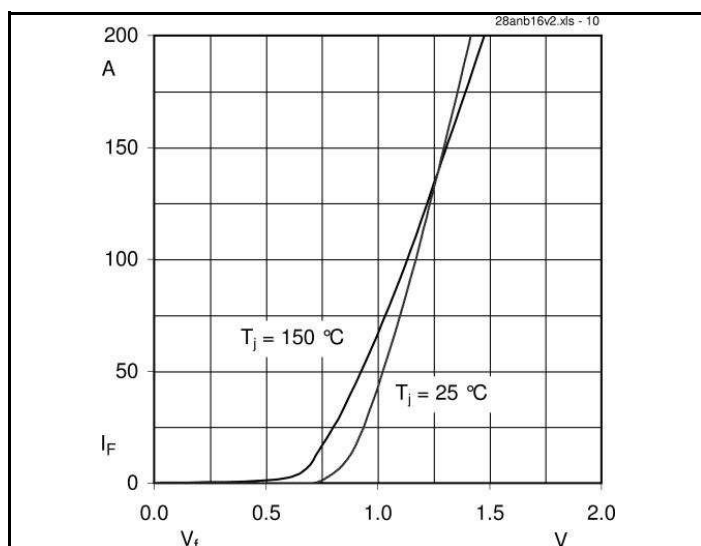
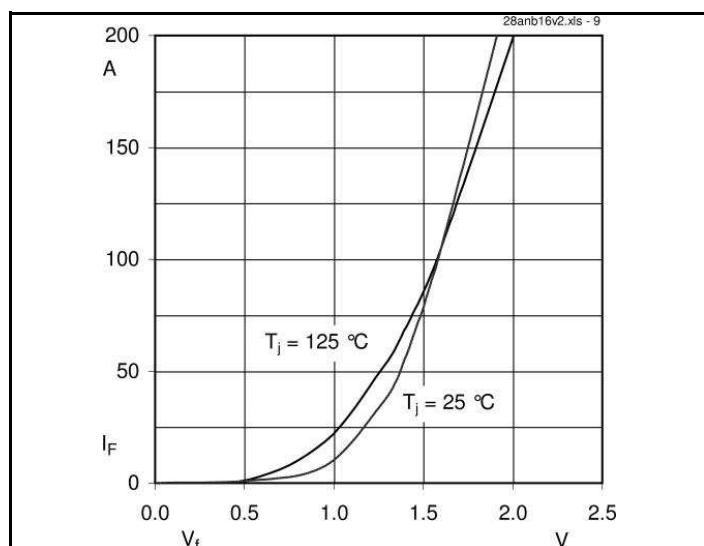
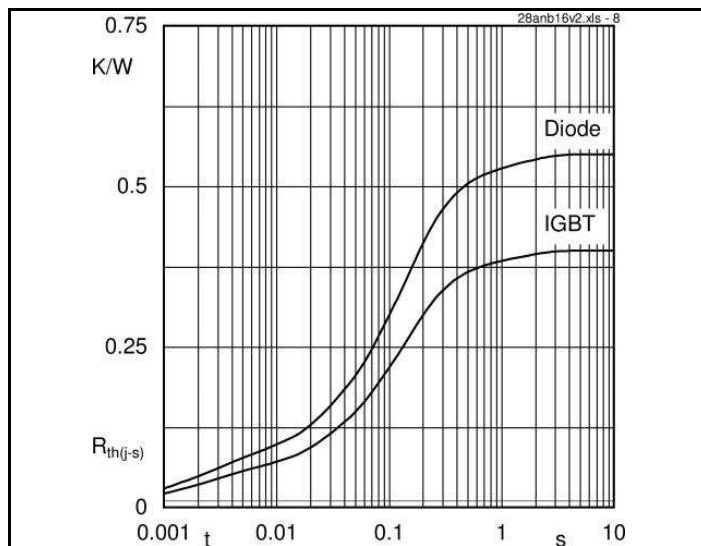
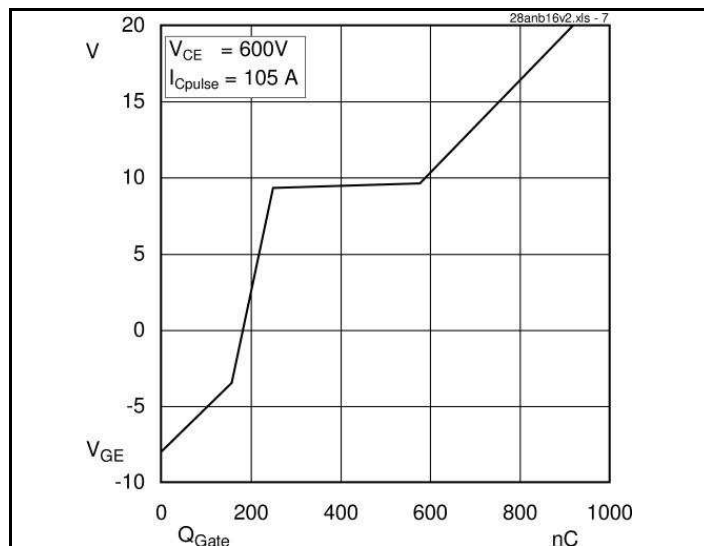


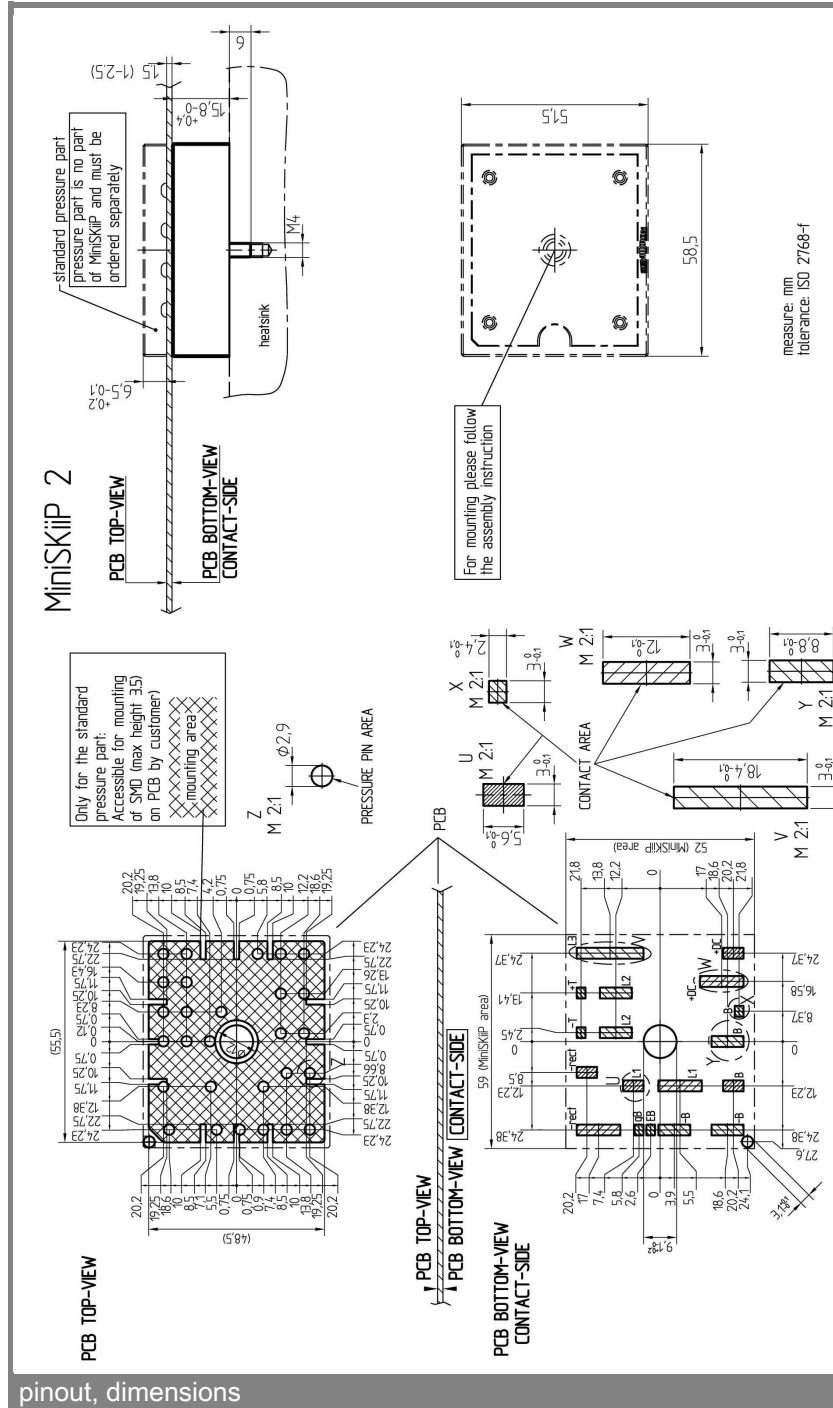
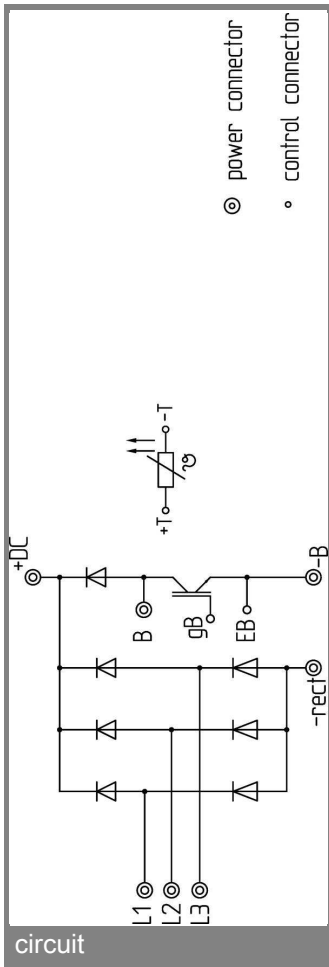
ANB

Absolute Maximum Ratings		T _s = 25 °C, unless otherwise specified	
Symbol	Conditions	Values	Units
IGBT - Chopper			
V _{CES}	T _s = 25 (70) °C	1200	V
I _C		118 (88)	A
I _{CRM}		210	A
V _{GES}		± 20	V
T _j		- 40 ... + 150	°C
Diode - Chopper			
I _F	T _s = 25 (70) °C	118 (88)	A
I _{FRM}		210	A
T _j		- 40 ... + 150	°C
Diode - Rectifier			
V _{RRM}	T _s = 70 °C	1600	V
I _F		83	A
I _{FSM}		1000	A
i ² t		6600	A ² s
T _j		- 40 ... + 150	°C
Module			
I _{tRMS}	per power terminal (20 A / spring)	120	A
T _{stg}		- 40 ... + 125	°C
V _{isol}	AC, 1 min.	2500	V

Characteristics		$T_s = 25\text{ }^{\circ}\text{C}$, unless otherwise specified			
Symbol	Conditions	min.	typ.	max.	Units
IGBT - Chopper					
V_{CEsat}	$I_{Cnom} = 105\text{ A}$, $T_j = 25\text{ (125) }^{\circ}\text{C}$	5	1,7 (2)	2,1 (2,4)	V
$V_{GE(th)}$	$V_{GE} = V_{CE}$, $I_C = 3\text{ mA}$		5,8	6,5	V
$V_{CE(TO)}$	$T_j = 25\text{ (125) }^{\circ}\text{C}$		1 (0,9)	1,2 (1,1)	V
r_T	$T_j = 25\text{ (125) }^{\circ}\text{C}$		6,7 (10)	8,6 (12)	mΩ
C_{ies}	$V_{CE} = 25\text{ V}$, $V_{GE} = 0\text{ V}$, $f = 1\text{ MHz}$		8,4		nF
C_{oes}	$V_{CE} = 25\text{ V}$, $V_{GE} = 0\text{ V}$, $f = 1\text{ MHz}$		1,5		nF
C_{res}	$V_{CE} = 25\text{ V}$, $V_{GE} = 0\text{ V}$, $f = 1\text{ MHz}$		1,1		nF
$R_{th(j-s)}$	per IGBT		0,4		K/W
$t_{d(on)}$	under following conditions		65		ns
t_r	$V_{CC} = 600\text{ V}$, $V_{GE} = \pm 15\text{ V}$		30		ns
$t_{d(off)}$	$I_{Cnom} = 105\text{ A}$, $T_j = 125^{\circ}\text{C}$		465		ns
t_f	$R_{Gon} = R_{Goff} = 5,1\text{ }\Omega$		95		ns
E_{on}	inductive load		10,1		mJ
E_{off}			13,6		mJ
Diode - Chopper					
$V_F = V_{EC}$	$I_{Fnom} = 105\text{ A}$, $T_j = 25\text{ (125) }^{\circ}\text{C}$		1,6 (1,6)	1,8 (1,8)	V
$V_{(TO)}$	$T_j = 25\text{ (125) }^{\circ}\text{C}$		1 (0,8)	1,1 (0,9)	V
r_T	$T_j = 25\text{ (125) }^{\circ}\text{C}$		5,7 (7,6)	6,7 (8,6)	mΩ
$R_{th(j-s)}$	per diode		0,55		K/W
I_{RRM}	under following conditions		180		A
Q_{rr}	$I_{Fnom} = 105\text{ A}$, $V_R = 600\text{ V}$		26		μC
E_{rr}	$V_{GE} = 0\text{ V}$, $T_j = 125\text{ }^{\circ}\text{C}$ $di_F/dt = 4350\text{ A/}\mu\text{s}$		11,8		mJ
Diode - Rectifier					
V_F	$I_{Fnom} = 75\text{ A}$, $T_j = 25\text{ }^{\circ}\text{C}$		1,2		V
$V_{(TO)}$	$T_j = 150\text{ }^{\circ}\text{C}$		0,8		V
r_T	$T_j = 150\text{ }^{\circ}\text{C}$		7		mΩ
$R_{th(j-s)}$	per diode		0,7		K/W
Temperature Sensor					
R_{ts}	3 %, $T_r = 25\text{ (100) }^{\circ}\text{C}$		1000(1670)		Ω
Mechanical Data					
w			65		g
M_s	Mounting torque	2		2,5	Nm







This is an electrostatic discharge sensitive device (ESDS), international standard IEC 60747-1, Chapter IX.

This technical information specifies semiconductor devices but promises no characteristics. No warranty or guarantee expressed or implied is made regarding delivery, performance or suitability.